

MGFC36V5258

5.2~5.8GHz BAND 4W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC36V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 ~ 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

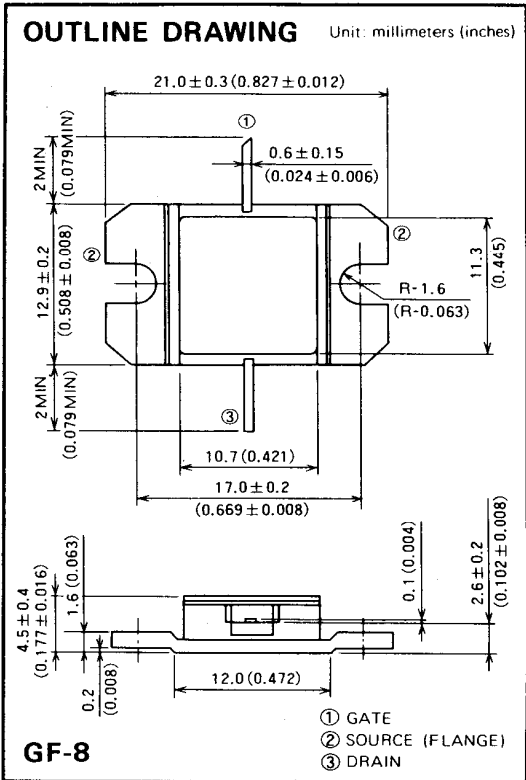
- Class A operation
- Internally matched to 50Ω system
- High output power
 $P_{1dB} = 4\text{ W (TYP) @ } 5.2 \sim 5.8\text{ GHz}$
- High power gain
 $G_{LP} = 10\text{ dB (TYP) @ } 5.2 \sim 5.8\text{ GHz}$
- High power added efficiency
 $\eta_{add} = 32\% \text{ (TYP) @ } 5.2 \sim 5.8\text{ GHz, } P_{1dB}$
- Hermetically sealed metal-ceramic package

APPLICATION

5.2 ~ 5.8 GHz band power amplifiers.

QUALITY GRADE

- IG



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Ratings	Unit
V_{GDO}	Gate to drain voltage	-15	V
V_{GSO}	Gate to source voltage	-15	V
I_D	Drain current	2.8	A
I_{GR}	Reverse gate current	-10	mA
I_{GF}	Forward gate current	+21	mA
P_T	Total power dissipation *1	25	W
T_{ch}	Channel temperature	175	$^\circ\text{C}$
T_{stg}	Storage temperature	-65 ~ +175	$^\circ\text{C}$

*1: $T_C = 25^\circ\text{C}$

RECOMMENDED BIAS CONDITIONS

- $V_{DS} = 10\text{V}$
- $I_D = 1.2\text{A}$
- $R_g = 100\Omega$
- Refer to Bias Procedure

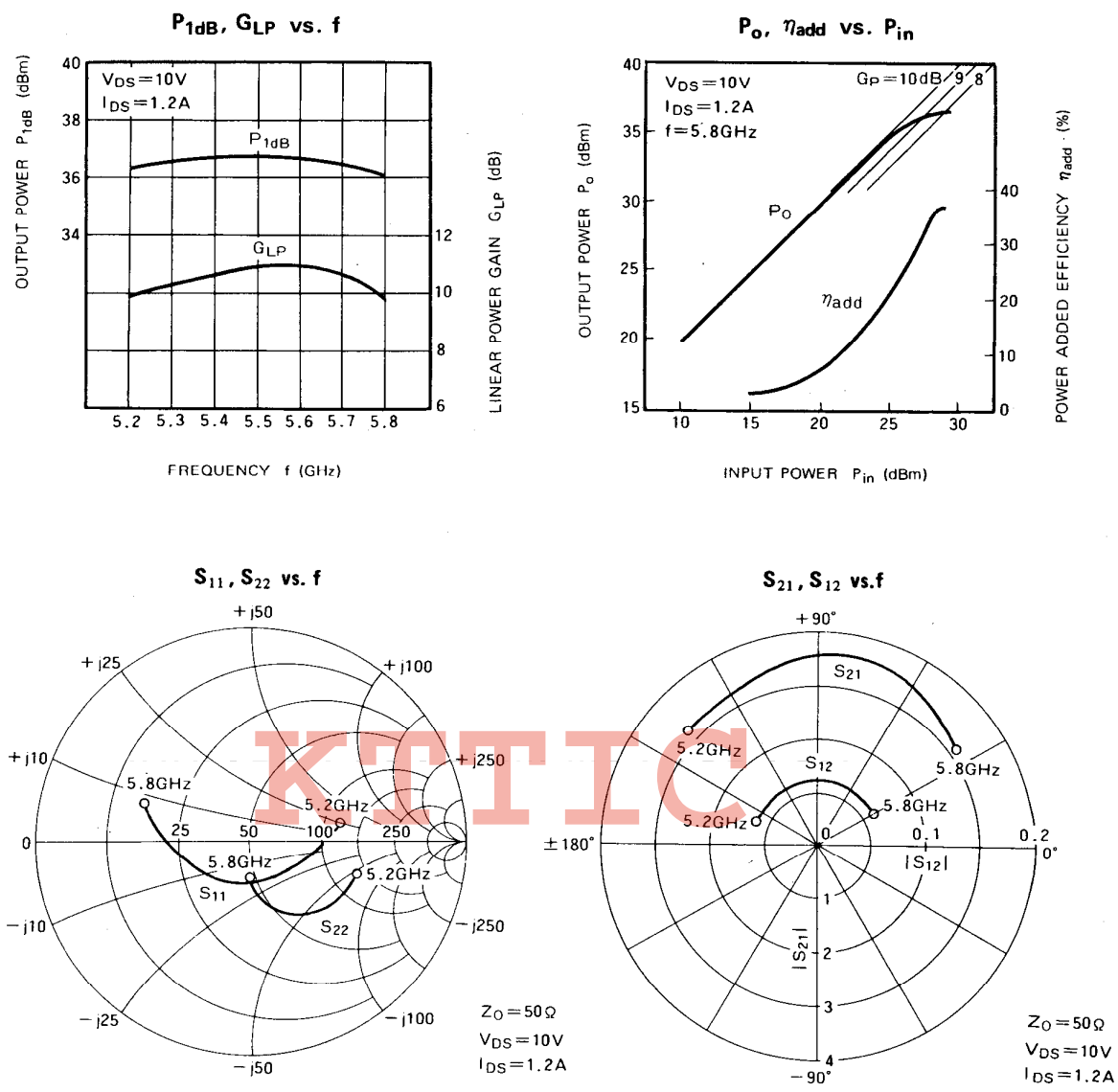
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I_{DSS}	Saturated drain current	$V_{DS} = 3\text{V}, V_{GS} = 0\text{V}$	—	2.0	2.8	A
g_m	Transconductance	$V_{DS} = 3\text{V}, I_D = 1.1\text{A}$	—	1.0	—	S
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS} = 3\text{V}, I_D = 10\text{mA}$	-2	-3	-4	V
P_{1dB}	Output power at 1dB gain compression	$V_{DS} = 10\text{V}, I_D = 1.2\text{A}, f = 5.2 \sim 5.8\text{GHz}$	35	36	—	dBm
G_{LP}	Linear power gain		9	10	—	dB
I_D	Drain current		—	1.1	1.4	A
η_{add}	Power added efficiency		—	33	—	%
$R_{th(ch-c)}$	Thermal resistance *1	ΔV_f method	—	—	6	$^\circ\text{C/W}$

*1: Channel to case

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TYPICAL CHARACTERISTICS (Ta=25°C)



S PARAMETERS (Ta=25°C, VDS=10V, IDS=1.2A)

f (GHz)	S Parameters (TYP.)							
	S_{11}		S_{21}		S_{12}		S_{22}	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
5.2	0.43	13	3.27	138	0.062	156	0.51	-17
5.3	0.30	-3	3.30	122	0.062	138	0.48	-28
5.4	0.19	-41	3.45	105	0.062	120	0.46	-39
5.5	0.18	-99	3.61	89	0.060	102	0.41	-51
5.6	0.28	-152	3.61	73	0.061	78	0.34	-66
5.7	0.39	179	3.45	55	0.059	56	0.26	-80
5.8	0.51	161	3.19	36	0.058	32	0.17	-98

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